

Replacement Abstract

A method for heating a wafer to a predetermined temperature, the wafer being held by a holding unit and being accommodated in a processing container equipped with a heater. The wafer is heated to a processing temperature while positioning the wafer at an adjacent position that results from making the wafer approach the heating surface of the heater. After heating the wafer to the predetermined temperature, the wafer is separated from the flat bottom surface of the container body to a processing position. In this state, a processing chamber of the processing container is supplied with a processing fluid, while the holding unit and the heater are relatively moved close to and apart from each other intermittently or continuously. Accordingly, it is possible to quickly heat the substrate to a processing temperature while supplying the substrate with the processing fluid uniformly. This improves throughput and the homogenization in processing.